



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	60A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	12m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	15m



YJR60G10A

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
		$V_{DS}=100V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	I					



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Typical Electrical and Thermal Characteristics Diagrams

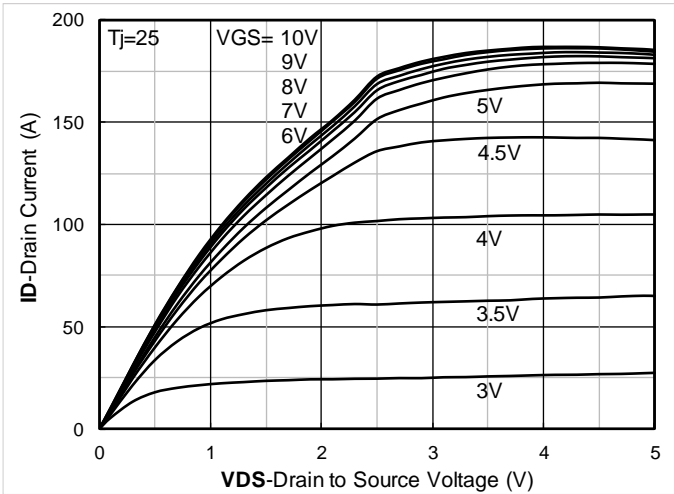


Figure 1. Output Characteristics

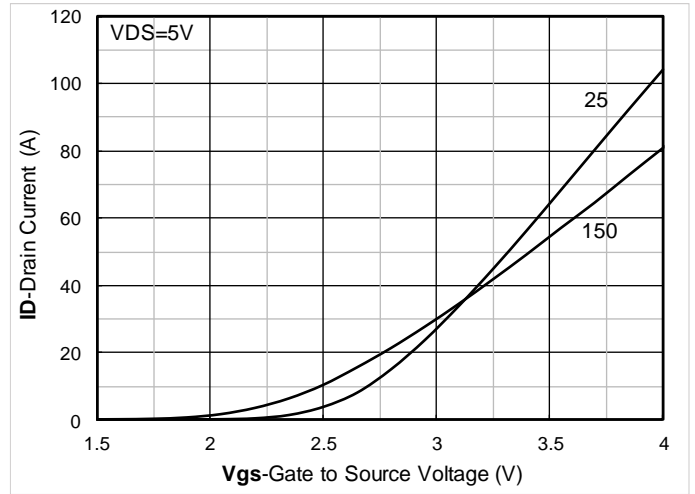


Figure 2. Transfer Characteristics

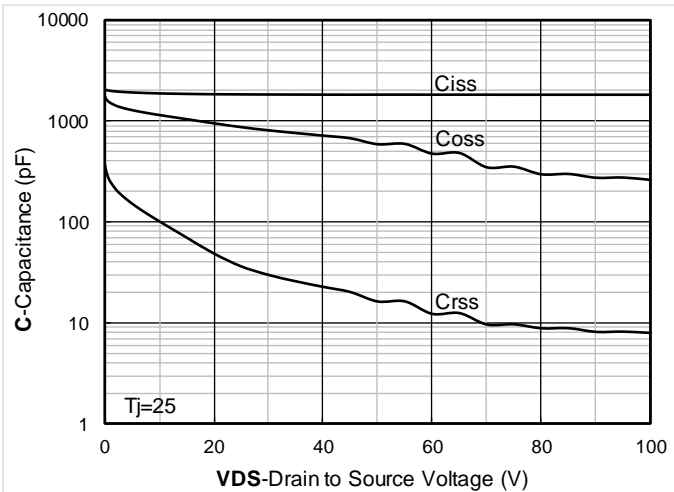


Figure 3. Capacitance Characteristics

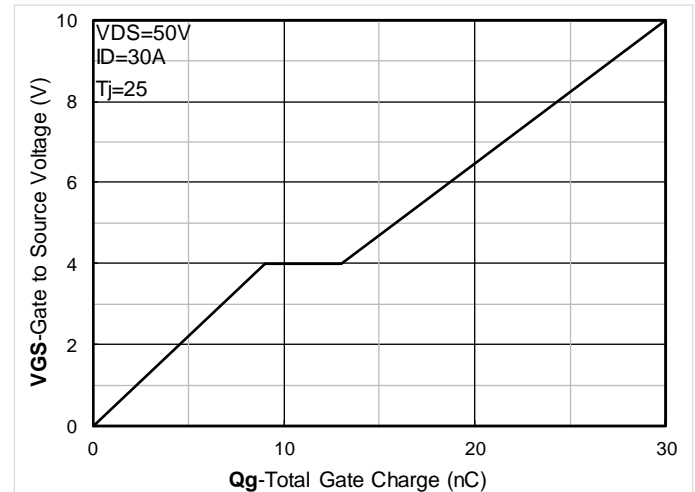


Figure 4. Gate Charge

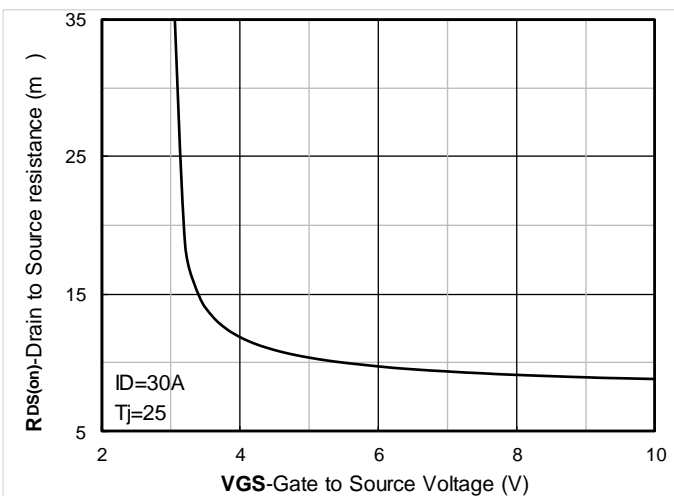


Figure 5. On-Resistance vs Gate to Source Voltage

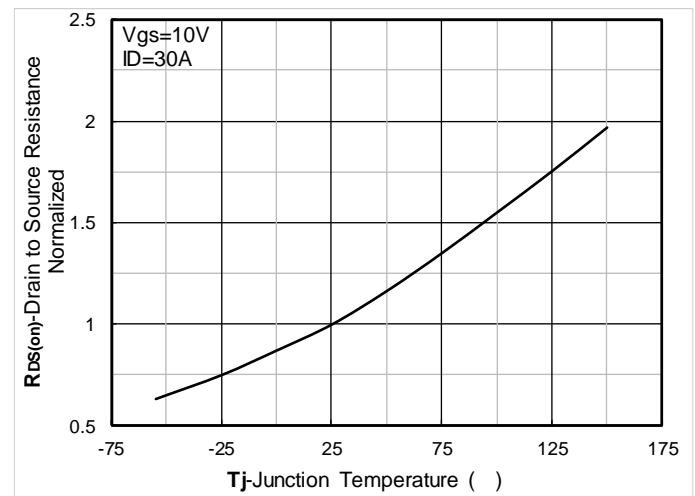


Figure 6. Normalized On-Resistance



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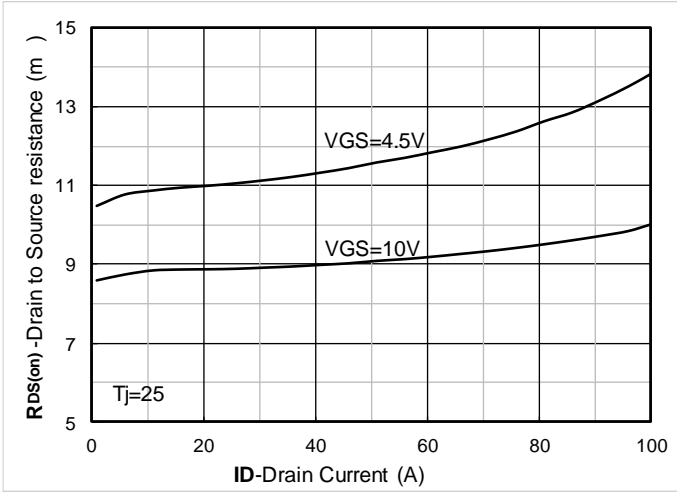


Figure 7. RDS(on) VS Drain Current

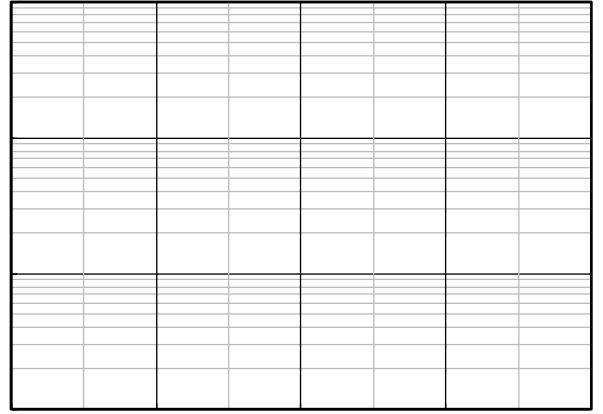


Figure 8. Forward characteristics of reverse diode

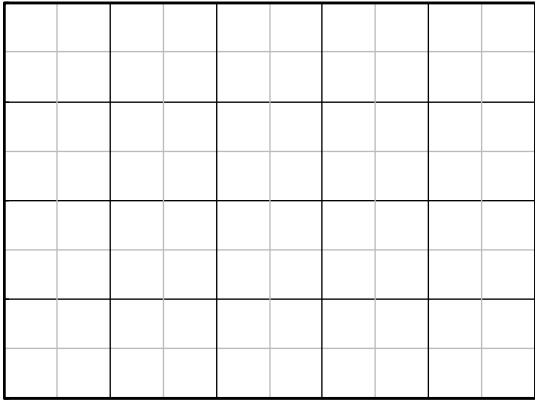


Figure 9. Normalized breakdown voltage

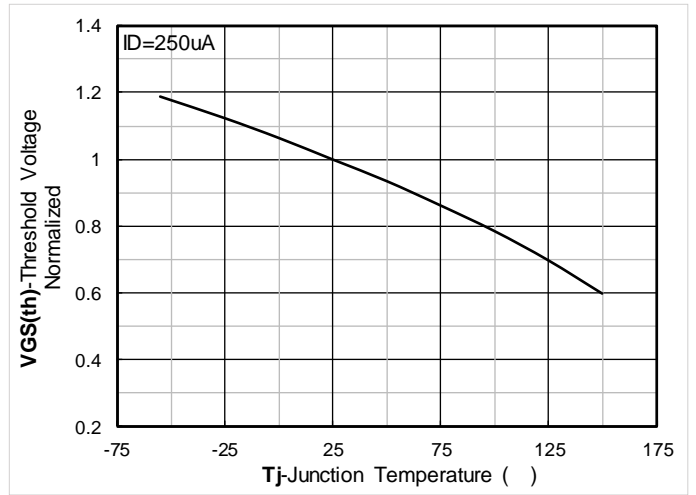


Figure 10. Normalized Threshold voltage

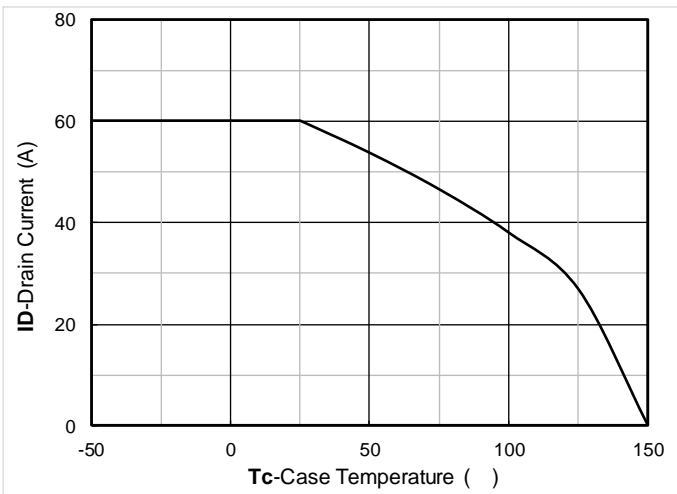
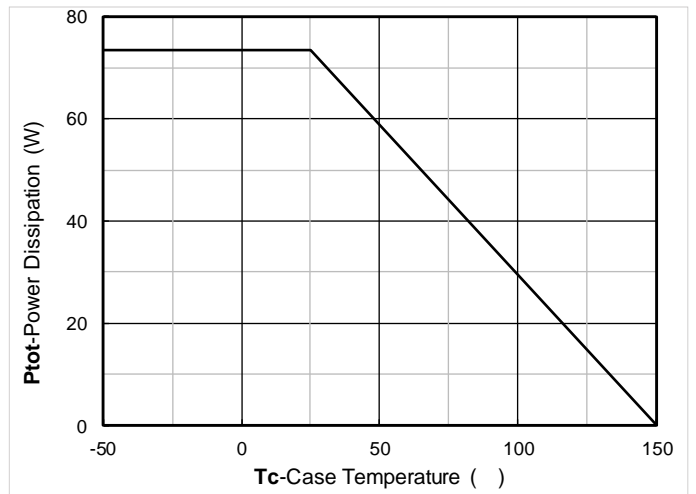


Figure 11. Current dissipation



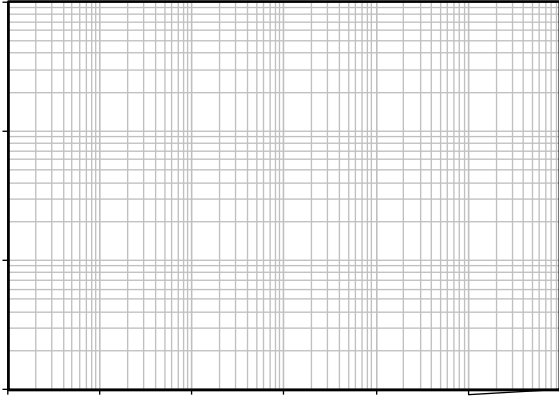


Figure 13. Maximum Transient Thermal Impedance

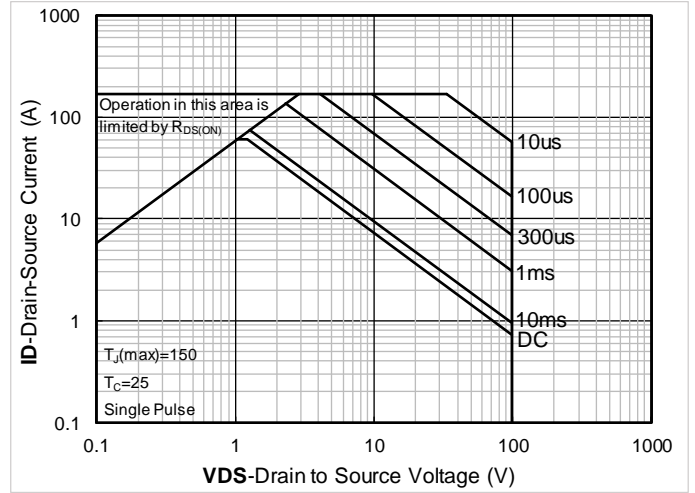


Figure 14. Safe Operation Area

Test Circuits & Waveforms

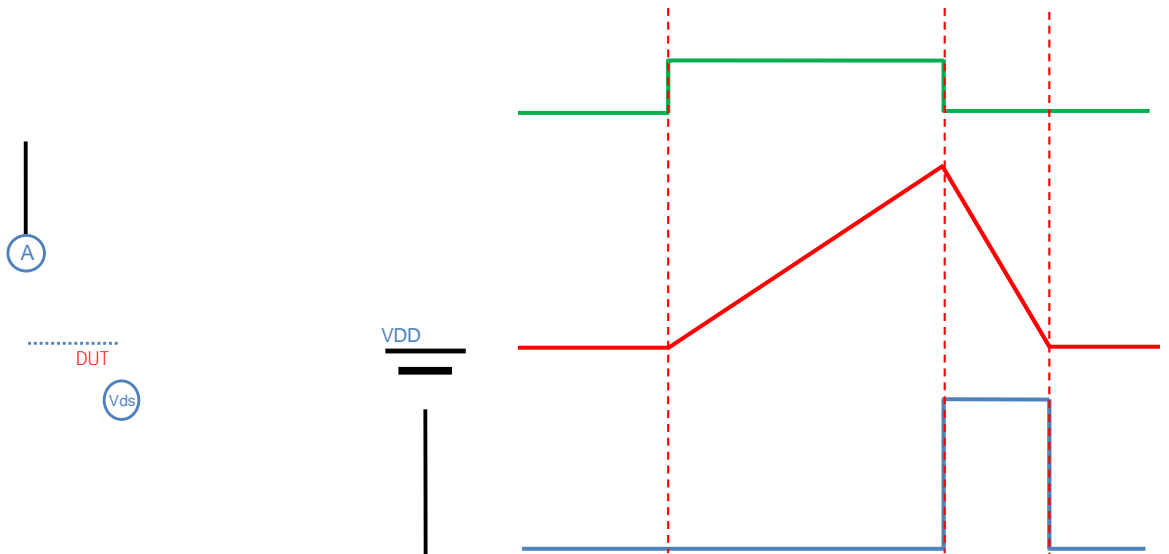


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



Figure B. Gate Charge Test Circuit & Waveform

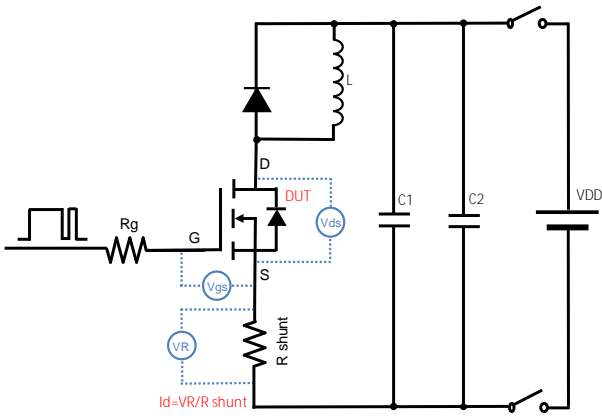


Figure C. Resistive Switching Test Circuit & Waveform



Figure D. Diode Recovery Test Circuit & Waveform



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TO-251S Package information



